

Serial No. 09/935,352

PATENT  
Docket No. 58027-011900

**Claim 75 (new):** The method for aperturing a VCSEL according to claim 35, further comprising etching at least one of the first and the second cladding surface with a reactive ion etch.

**Claim 76 (new):** The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 55, wherein the at least one material includes Al.

**Claim 77 (new):** The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 55, wherein the at least one material includes Ga.

**Claim 78 (new):** The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 1, wherein the first and the second cladding surfaces are made of InP.

**Claim 79 (new):** The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 1, wherein the aperture layer is an active region.

**Claim 80 (new):** The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 4, wherein the aperture layer is an active region.

**Claim 81 (new):** The vertical-cavity surface-emitting laser (VCSEL) according to claim 10, wherein the aperture layer is an active region.

**Claim 82 (new):** The vertical-cavity surface-emitting laser (VCSEL) according to claim 10, wherein the aperture layer is comprised of InAlGaAs.

**Claim 83 (new):** The vertical-cavity surface-emitting laser (VCSEL) according to claim 10, wherein the first and the second cladding surfaces are made of InP.

**Claim 84 (new):** The vertical-cavity surface-emitting laser (VCSEL) according to claim 22, wherein the aperture layer is comprised of InAlGaAs.

**Claim 85 (new):** The vertical-cavity surface-emitting laser (VCSEL) according to claim 22, wherein the aperture layer is an active region.

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<sup>86</sup>  
Claim ~~88~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 35, wherein the first and the second cladding layers are made of InP.

<sup>87</sup>  
Claim ~~89~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 35, wherein the aperture layer is an active region.

<sup>88</sup>  
Claim ~~90~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 35, wherein the aperture layer is comprised of InAlGaAs.

<sup>89</sup>  
Claim ~~91~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 51, wherein the at least one cladding surface is made of InP.

<sup>90</sup>  
Claim ~~92~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 51, wherein the aperture layer is comprised of InAlGaAs.

<sup>91</sup>  
Claim ~~93~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 51, wherein the aperture layer is an active region.

<sup>92</sup>  
Claim ~~94~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 55, wherein the aperture layer is comprised of InAlGaAs.

<sup>93</sup>  
Claim ~~95~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 55, wherein the aperture layer is an active region.

<sup>94</sup>  
Claim ~~96~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 61, wherein the aperture layer is comprised of InAlGaAs.

<sup>95</sup>  
Claim ~~97~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 61, wherein the aperture layer is an active region.

<sup>96</sup>  
Claim ~~98~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 61, wherein the cladding surfaces are made of InP.

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<sup>97</sup>  
Claim ~~99~~ (new): The method for aperturing a VCSEL according to claim 61, wherein the aperture is formed by selectively etching the aperture layer by an etchant composed of citric acid and hydrogen peroxide in a predetermined ratio.

<sup>98</sup>  
Claim ~~100~~ (new): The method for aperturing a vertical-cavity surface-emitting laser (VCSEL) according to claim 4, wherein the first and the second cladding surfaces are made of InP.